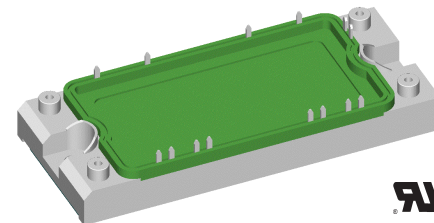
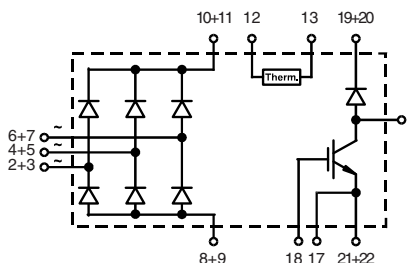


Three Phase Rectifier Bridge with IGBT and Fast Recovery Diode for Braking System

$$V_{RRM} = 1600 \text{ V}$$

$$I_{dAVM} = 116/145 \text{ A}$$

V_{RRM} V	Type
1600	VUB 116-16 NO1
1600	VUB 145-16 NO1



Pin arrangement see outline drawing

Symbol	Conditions	Maximum Ratings	
		VUB 116	VUB 145
V_{RRM}	$T_C = 100^\circ\text{C}$, sinusoidal 120°	1600	1600
I_{dAVM}		116	145
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$, $t = 10 \text{ ms}$, $V_R = 0 \text{ V}$	700	1100
	$T_{VJ} = 150^\circ\text{C}$, $t = 10 \text{ ms}$, $V_R = 0 \text{ V}$	610	960
I^2t	$T_{VJ} = 45^\circ\text{C}$, $t = 10 \text{ ms}$, $V_R = 0 \text{ V}$	2450	6050
	$T_{VJ} = 150^\circ\text{C}$, $t = 10 \text{ ms}$, $V_R = 0 \text{ V}$	1860	4610
P_{tot}	$T_C = 25^\circ\text{C}$ per diode	190	250
V_{CES}	$T_{VJ} = 25^\circ\text{C}$ to 150°C Continuous	1200	1200
V_{GE}		± 20	± 20
I_{C25}	$T_C = 25^\circ\text{C}$, DC	95	141
I_{C80}		67	100
I_{CM}	$t_p = \text{Pulse width limited by } T_{VJM}$	100	150
P_{tot}	$T_C = 25^\circ\text{C}$	380	570
V_{RRM}	$T_C = 80^\circ\text{C}$, rectangular $d = 0.5$	1200	
I_{FAV}		27	
I_{FRMS}	$T_C = 80^\circ\text{C}$, rectangular $d = 0.5$	38	
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$, $t = 10 \text{ ms}$	200	
P_{tot}	$T_C = 25^\circ\text{C}$	130	
T_{VJ}	Operating	-40...+125	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, $t = 1 \text{ min}$	2500	V~
	$I_{ISOL} \leq 1 \text{ mA}$, $t = 1 \text{ s}$	3000	V~
M_d	Mounting torque	2.7...3.3	Nm
d_s	Creep distance on surface	12.7	mm
d_A	Strike distance in air	9.6	mm
a	Maximum allowable acceleration	50	m/s^2
$R_{pin-chip}$		typ. 2	$\text{m}\Omega$
Weight	typ.	180	g

Features

- Soldering connections for PCB mounting
- Convenient package outline
- Thermistor
- UL registered, E 153432

Applications

- Drive Inverters with brake system

Advantages

- 2 functions in one package
- Easy to mount with two screws
- Suitable for wave soldering
- High temperature and power cycling capability

Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions.

20080513b

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_R	$V_R = V_{RRM}, T_{VJ} = 25^{\circ}\text{C}$ $V_R = V_{RRM}, T_{VJ} = 150^{\circ}\text{C}$			0.1 mA 2 mA
V_F	$I_F = 80\text{ A}, T_{VJ} = 25^{\circ}\text{C}$ $I_F = 150\text{ A}, T_{VJ} = 25^{\circ}\text{C}$	VUB 116 VUB 145		1.43 V 1.68 V
V_{T0}	for power-loss calculations only	VUB 116 VUB 145		0.85 V 0.85 V
r_T	$T_{VJ} = 150^{\circ}\text{C}$	VUB 116 VUB 145		7.1 mΩ 5.9 mΩ
R_{thJC}	per diode	VUB 116 VUB 145		0.65 K/W 0.5 K/W
R_{thCH}	per diode	VUB 116 VUB 145		0.1 K/W 0.1 K/W
$V_{BR(CES)}$	$V_{GS} = 0\text{ V}, I_C = 0.1\text{ mA}$	1200		V
$V_{GE(th)}$	$I_C = 8\text{ mA}$ $I_C = 3\text{ mA}$	VUB 116 VUB 145	4.5 4.5	6.45 V 6.45 V
I_{CES}	$T_{VJ} = 25^{\circ}\text{C}, V_{CE} = 1200\text{ V}$ $T_{VJ} = 125^{\circ}\text{C}, V_{CE} = 0.8 \cdot V_{CES}$			0.1 mA 0.5 mA
V_{CEsat}	$V_{GE} = 15\text{ V}, I_C = 100\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 150\text{ A}$	VUB 116 VUB 145		3.5 V 3.7 V
$t_{SC}(\text{SCSOA})$	$V_{GE} = 15\text{ V}, V_{CE} = 720\text{ V}, T_{VJ} = 125^{\circ}\text{C}$,			10 μs
RBSOA	$V_{GE} = 15\text{ V}, V_{CE} = 1200\text{ V}, T_{VJ} = 125^{\circ}\text{C}$, clamped inductive load, $L = 100\text{ μH}$ $R_G = 22\text{ Ω}$ $R_G = 15\text{ Ω}$	VUB 116 VUB 145		100 A 150 A
C_{ies}	$V_{CE} = 25\text{ V}, f = 1\text{ MHz}, V_{GE} = 0\text{ V}$	VUB 116 VUB 145	3.8 5.7	nF nF
$t_{d(on)}$	$V_{CE} = 720\text{ V}, I_C = 50/75\text{ A}$ $V_{GE} = 15\text{ V}, R_G = 22/15\text{ Ω}$ Inductive load; $L = 100\text{ μH}$ $T_{VJ} = 125^{\circ}\text{C}$	VUB 116 VUB 145	150 80	ns ns
$t_{d(off)}$			680	ns
E_{on}		VUB 116 VUB 145	6 9	mJ mJ
E_{off}		VUB 116 VUB 145	4 7.5	mJ mJ
R_{thJC}		VUB 116 VUB 145		0.33 K/W 0.22 K/W
R_{thJH}		VUB 116 VUB 145		0.66 K/W 0.44 K/W
I_R	$V_R = V_{RRM}, T_{VJ} = 25^{\circ}\text{C}$ $V_R = 1200\text{ V}, T_{VJ} = 125^{\circ}\text{C}$		1	0.25 mA mA
V_F	$I_F = 30\text{ A}, T_{VJ} = 25^{\circ}\text{C}$			2.76 V
V_{T0}	For power-loss calculations only			1.3 V
r_T	$T_{VJ} = 150^{\circ}\text{C}$			16 mΩ
I_{RM}	$I_F = 50\text{ A}, -di_F/dt = 100\text{ A/μs}, V_R = 100\text{ V}$		5.5	11 A
t_{rr}	$I_F = 1\text{ A}, -di_F/dt = 200\text{ A/μs}, V_R = 30\text{ V}$		40	ns
R_{thJC}				0.9 K/W
R_{thCH}				0.1 K/W
R_{25}	NTC	4.75	5.0	kΩ
$B_{25/50}$			3375	K

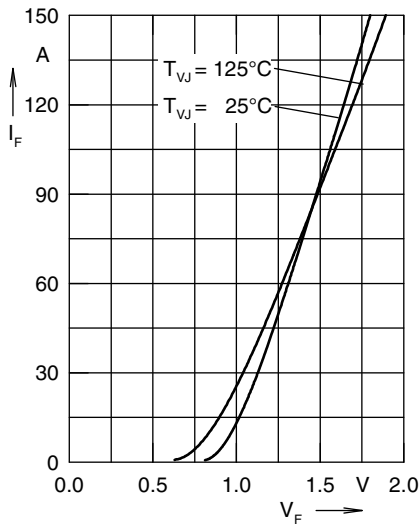


Fig. 1 Forward current vs. voltage drop per diode

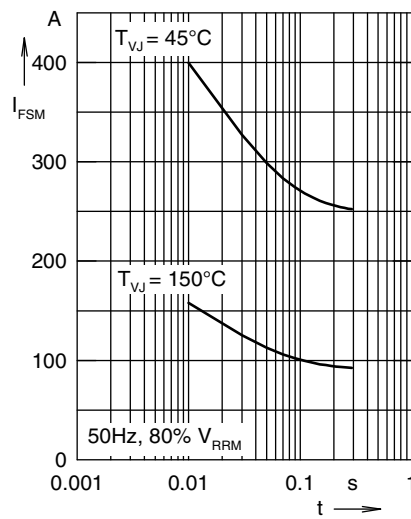


Fig. 2 Surge overload current

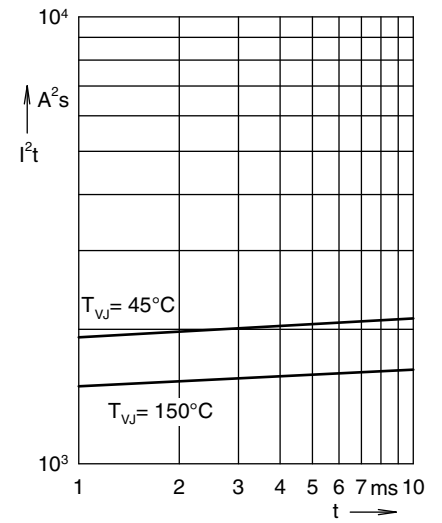


Fig. 3 I^2t versus time per diode

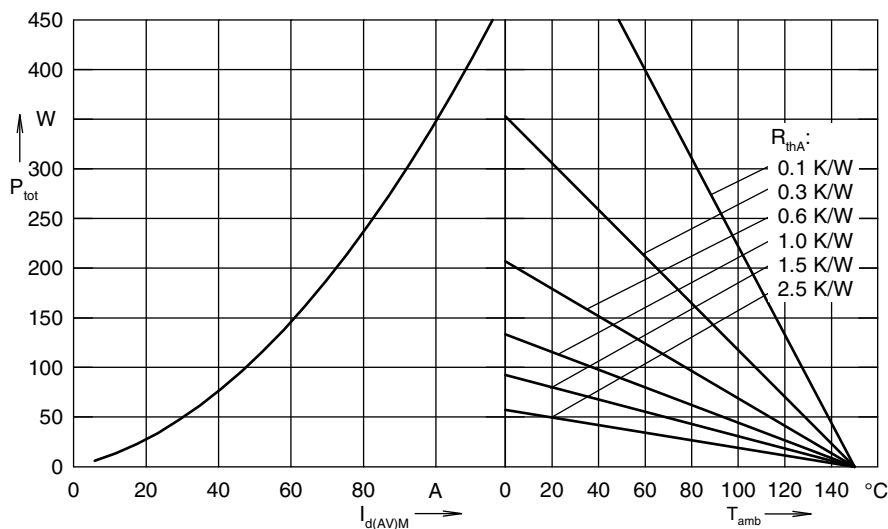


Fig. 4 Power dissipation versus direct output current and ambient temperature, sine 180°

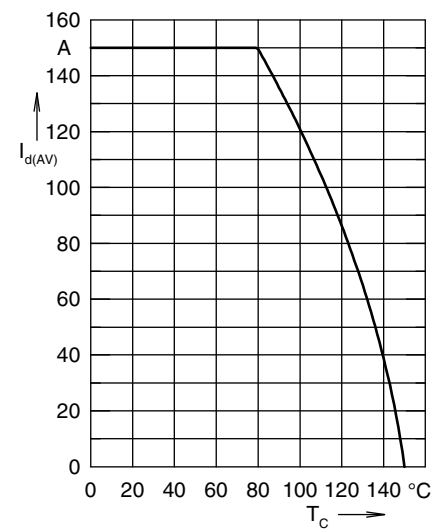


Fig. 5 Max. forward current vs. case temperature

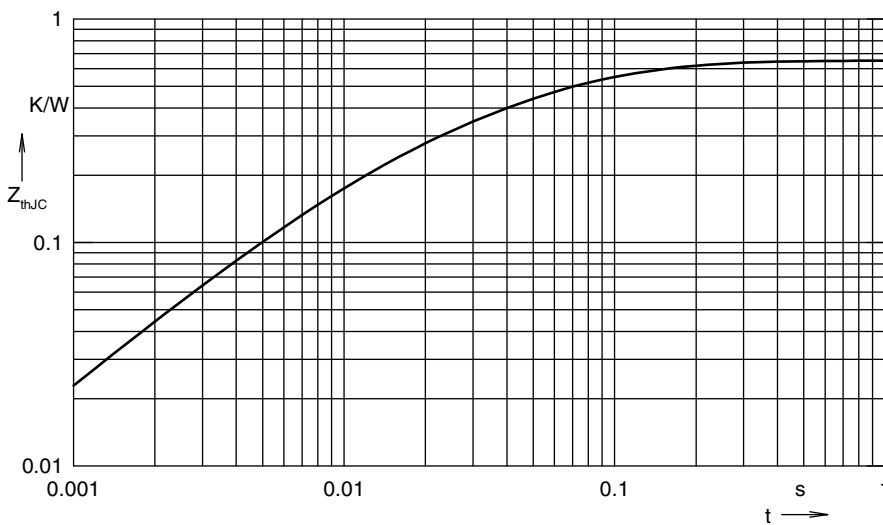


Fig. 6 Transient thermal impedance junction to case

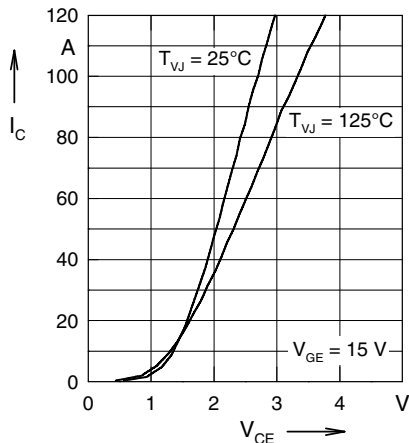


Fig. 7 Typ. output characteristics

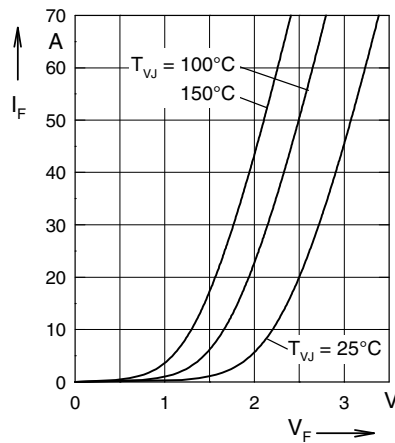


Fig. 8 Typ. forward characteristics of free wheeling diode

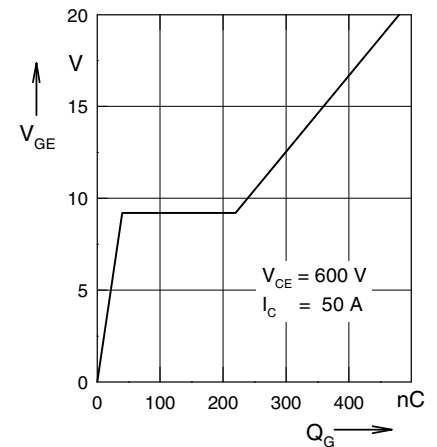


Fig. 9 Typ. turn on gate charge

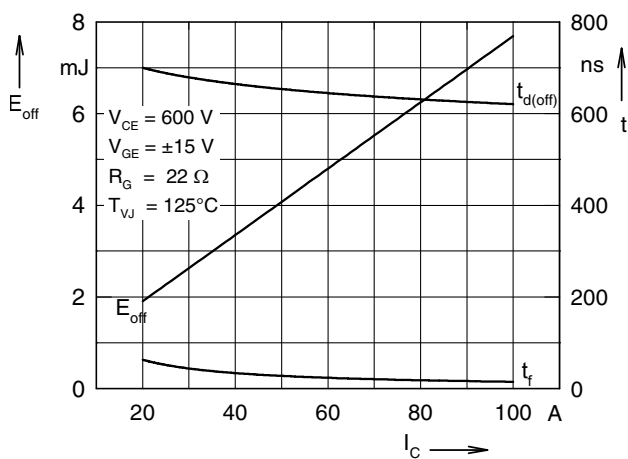


Fig. 10 Typ. turn off energy and switching times versus collector current

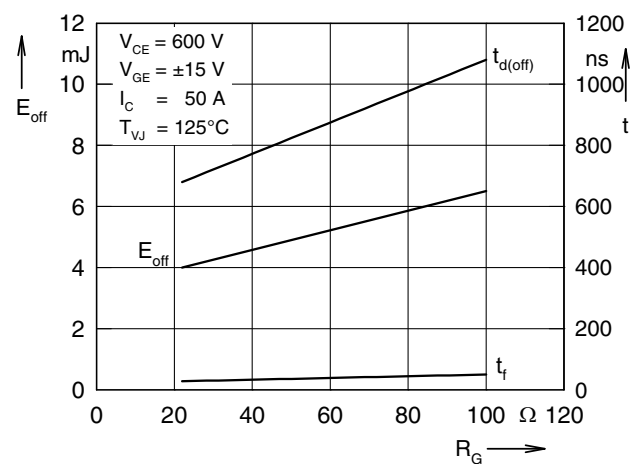


Fig. 11 Typ. turn off energy and switching times versus gate resistor

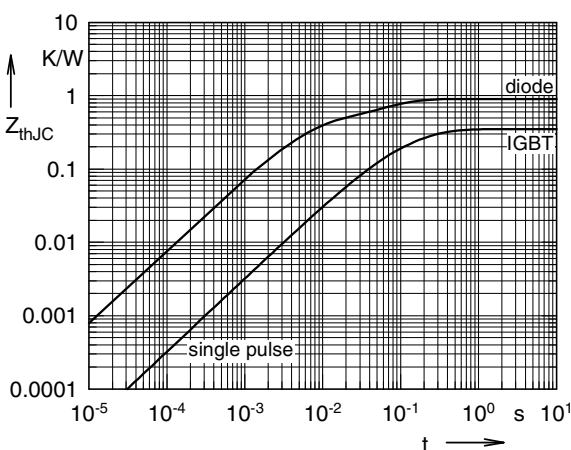


Fig. 12 Typ. transient thermal impedance

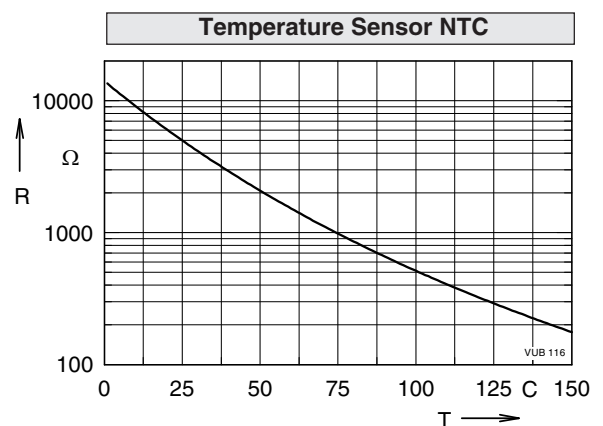


Fig. 13 Typ. thermistor resistance versus temperature

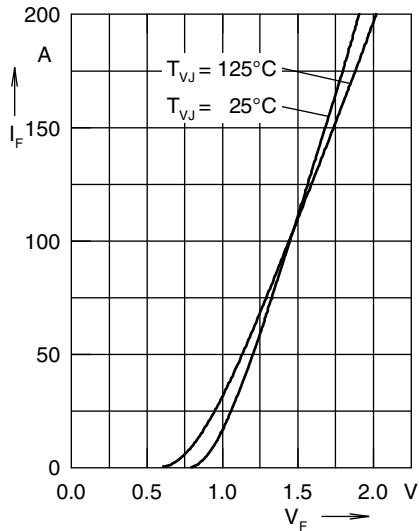


Fig. 1 Forward current versus voltage drop per diode

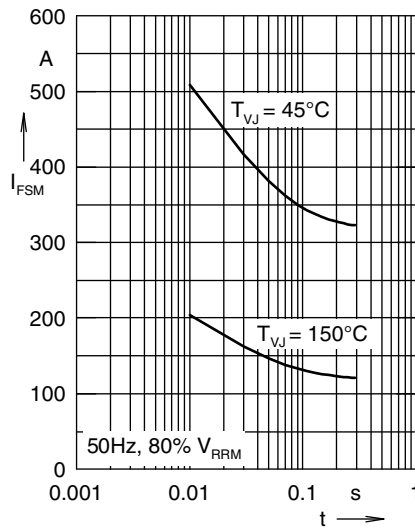


Fig. 2 Surge overload current

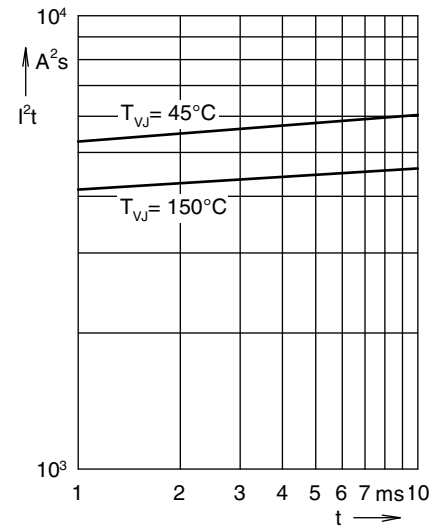


Fig. 3 I^2t versus time per diode

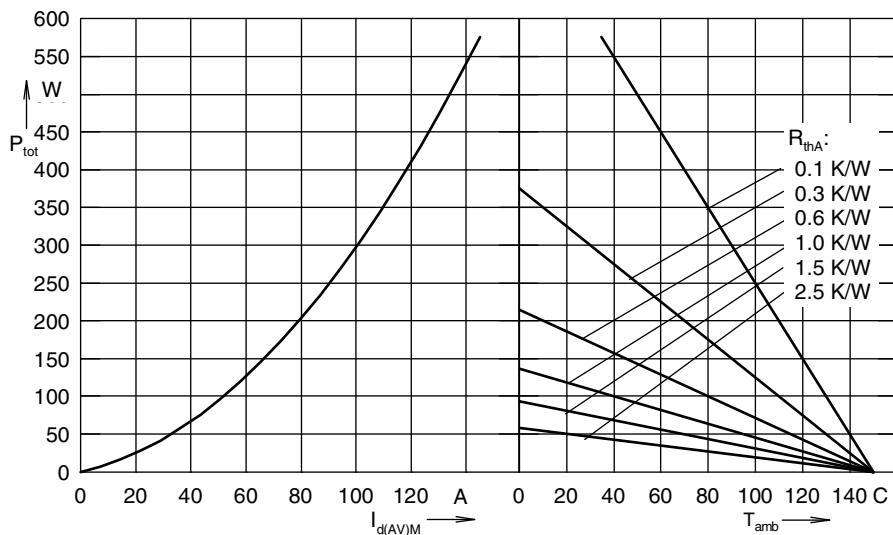


Fig. 4 Power dissipation vs. direct output current and ambient temperature, sin 180°

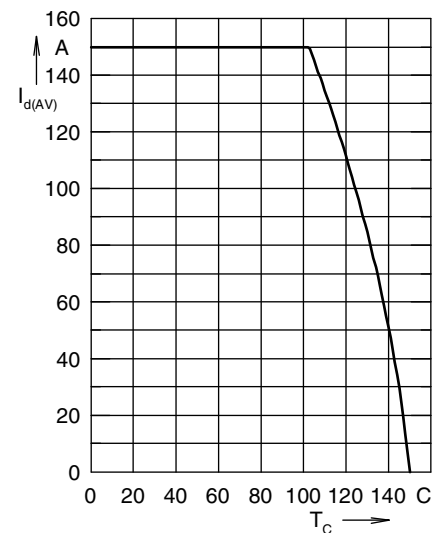


Fig. 5 Max. forward current vs. case temperature

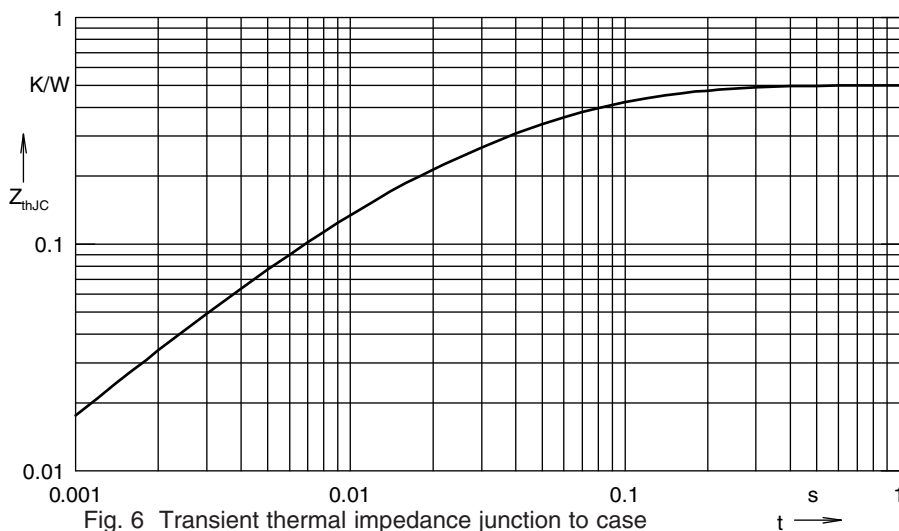


Fig. 6 Transient thermal impedance junction to case

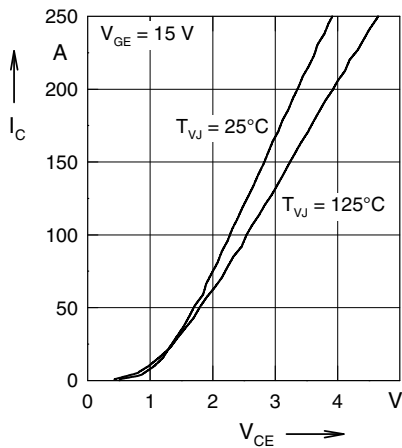


Fig. 7 Typ. output characteristics

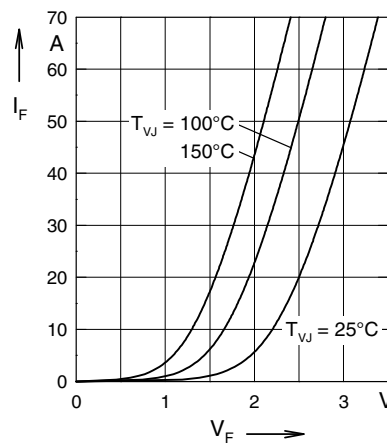


Fig. 8 Typ. forward characteristics of free wheeling diode

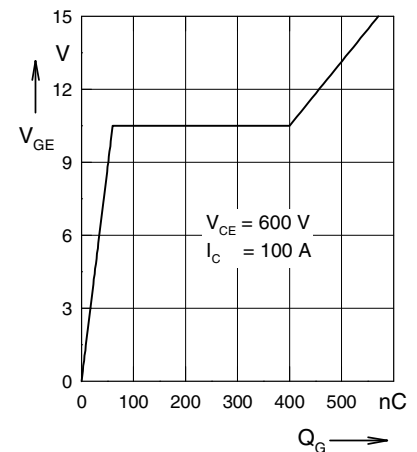


Fig. 9 Typ. turn on gate charge

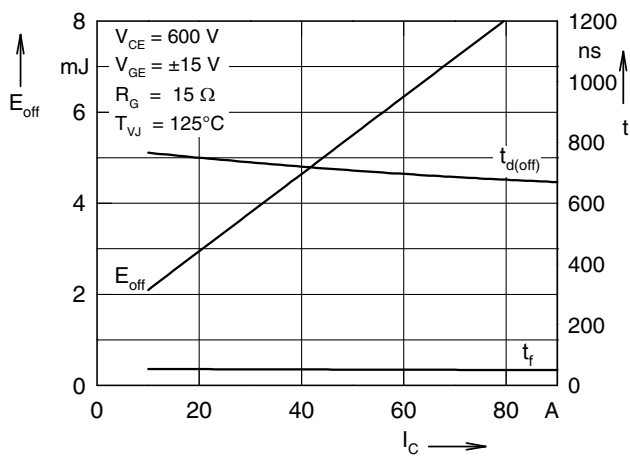


Fig. 10 Typ. turn off energy and switching times versus collector current

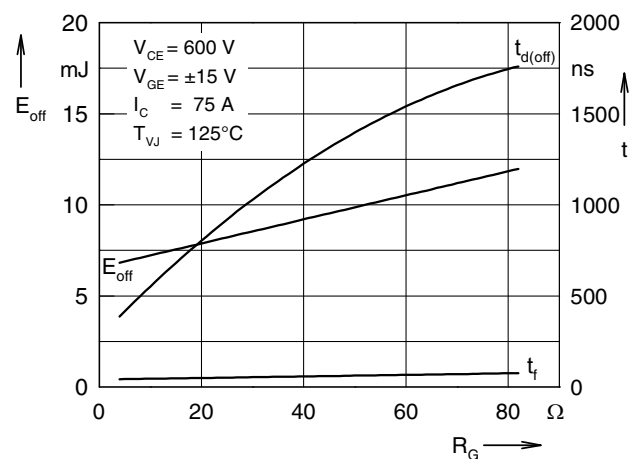


Fig. 11 Typ. turn off energy and switching times versus gate resistor

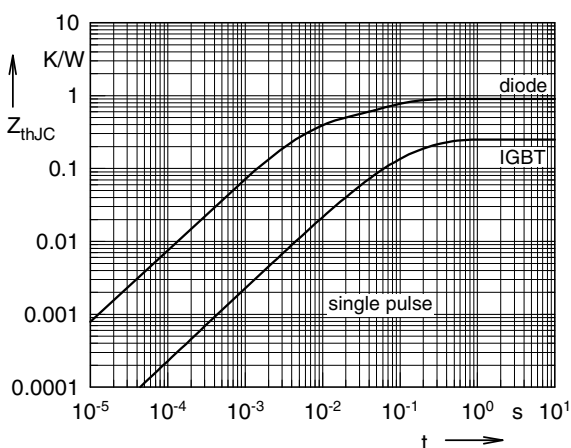


Fig. 12 Typ. transient thermal impedance

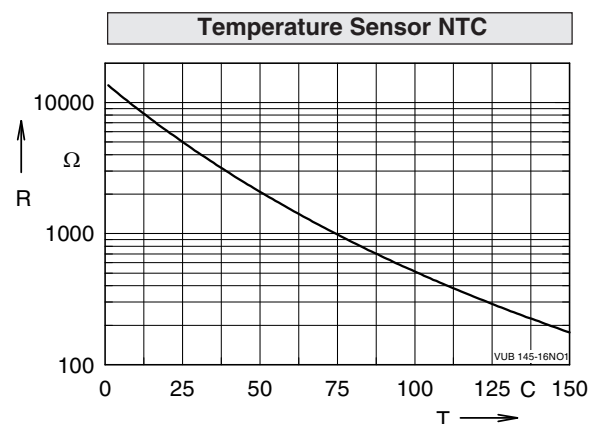


Fig. 13 Typ. thermistor resistance versus temperature